Velocity Saturation in La-doped BaSnO₃ Thin Films

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BaSnO₃, a high mobility perovskite oxide, is an attractive material for oxide-based electronic devices. However, in addition to low-field mobility, high-field transport properties such as the saturation velocity of carriers play a major role in determining device performance. We report on the experimental measurement of electron saturation velocity in La-doped BaSnO₃ thin films for a range of doping densities. Predicted saturation velocities based on an LO-phonon emission model show good agreement with measurements indicating that optical phonon emission is the likely mechanism for velocity saturation in La-doped BaSnO₃ films. Density-dependent saturation velocity in the range of 1.6x10⁷ cm/s reducing to 2x10⁶ cm/s is predicted for δ-doped BaSnO₃ channels with carrier densities ranging from 10¹³ cm⁻² to 2x10¹⁴ cm⁻² respectively. These results are expected to aid the informed design of BaSnO₃ as the active material for high-charge density electronic transistors.

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Perovskite oxides continue to attract a lot of interest for fundamental and applied physics in view of the plethora of electronic properties they exhibit.\(^1\) \(^2\) This also makes perovskites an ideal platform to integrate diverse device functionalities onto. However, the poor electron mobility of most perovskite oxides makes them a sub-optimal choice for electronic device applications. With a recorded room-temperature mobility of 320 cm\(^2\)/Vs in single-crystals,\(^3\) BaSnO\(_3\) (BSO) is a notable exception to this rule. The cause for such high mobility in BSO thin films has been studied previously and attributed both to the low effective mass of electrons owing to the significant anti-bonding \(s\)-orbital-like character of the conduction-band minimum,\(^4\) and the low electron-phonon scattering rate due to the lower density of conduction band states.\(^5\) Such high mobilities in conjunction with the large and tunable doping densities (\(~10^{20}\) cm\(^{-3}\)) achievable in this material, and the possibility of realizing heterostructures with carrier confinement makes BSO promising from an electronic device perspective.\(^6\) However, in addition to the low-field transport properties such as mobility, the operation of electronic devices such as RF amplifiers and highly-scaled transistors for logic depends critically on high-field transport, i.e. saturation velocity of charge carriers in the high-mobility channel.\(^7\) \(^8\) While low-field transport in BSO has been studied and modeled, there are no reports on high-field transport and the physical mechanisms limiting saturation velocity in this material, despite its relative importance for device performance. Here we report on the experimental measurement of saturation velocity in thin films of La-doped BSO and model its dependence on the dominant LO-phonon scattering process. We obtain reasonable agreement between the predicted and measured saturation velocities for an experimentally relevant range of doping densities which indicates that optical phonon emission is the likely mechanism for velocity saturation in BSO thin films.
TABLE I. Sample stack and thicknesses of the MBE-grown La-doped BSO thin films used in this study along with their measured sheet carrier concentrations (cm$^{-2}$) and Hall mobilities (cm$^2$/Vs).

<table>
<thead>
<tr>
<th>Sample Details</th>
<th>Sheet Carrier Concentration (cm$^{-2}$)</th>
<th>Mobility (cm$^2$/Vs)</th>
</tr>
</thead>
<tbody>
<tr>
<td>BTO/La:BSO/BSO/DSO (20 nm/21 nm/11 nm/substrate)</td>
<td>2.65 x 10$^{14}$</td>
<td>96</td>
</tr>
<tr>
<td>BTO/La:BSO/BSO/STO (20 nm/5 nm/16 nm/substrate)</td>
<td>1.92 x 10$^{14}$</td>
<td>87</td>
</tr>
<tr>
<td>La:BSO/BSO/STO (20 nm/5 nm/substrate)</td>
<td>7.23 x 10$^{13}$</td>
<td>58</td>
</tr>
</tbody>
</table>

FIG. 1. (a) Cross-section of a representative BSO thin film stack used in this study. (b) Schematic of the I-shaped test structure used for saturation velocity measurements. (c) SEM image of a fabricated test structure with the constriction mesa visible within the red dotted square (W=5 μm and L=1 μm).

BSO films were grown via MBE with various La concentrations on insulating (100) SrTiO$_3$ (STO) and (110) DyScO$_3$ (DSO) substrates, with and without BaTiO$_3$ (BTO) capping layers, as summarized in Table I. Due to the lattice mismatch between BSO and STO/DSO, all films are relaxed. For samples with a BTO capping layer, 20 nm of BTO was grown on the BSO film via hybrid MBE. Saturation velocity was measured on specially designed I-shaped test structures (Fig. 1) consisting of wide source and drain contact pads with a narrow mesa-defined
channel connecting them. Such a structure not only confines the current flow and applied potential to the channel, but also reduces any extraneous voltage drop in the contact/access regions due to the large difference in areas between the channel and contact regions.\textsuperscript{11} Device fabrication consisted of i-line stepper lithography for all layers commencing with Ti/Al alignment markers, inductively coupled plasma-reactive ion etching (ICP-RIE) of the BTO cap layer using BCl\textsubscript{3}/Ar, followed by ohmic contact deposition (Ti/Al, 50 nm/100 nm) using e-beam evaporation and finishing with an ICP-RIE (BCl\textsubscript{3}/Ar) mesa-etch of the BSO channel to define the I-shaped constrictions. Various constriction widths (2 μm, 5 μm and 10 μm) and lengths (600 nm to 2 μm) were fabricated and tested on each sample. Pulsed I-V measurements (1 μs pulse width, 0.1% duty cycle) were performed using a Keithley 4200 semiconductor characterization system on the test structures. Saturation velocity was extracted as $v_{sat} = J/qn_s$, where $J$ and $n_s$ are measured saturation current density (A/mm) and sheet carrier concentration (cm\textsuperscript{-2}) respectively, and plotted as a function of electric field as shown in Fig. 2 for the sample with $n_s=2.65 \times 10^{14}$ cm\textsuperscript{-2} as an example (Figs. S2 of the supplementary material show E vs J plots for the complete set of measured devices across all samples used in this study).\textsuperscript{12} Saturation current densities ranging from 5-50 A/mm were observed for the range of sample doping densities and we also observed device-device variation across each sample comparable to that shown in Fig. 2, which we attribute to local doping variations in the deposited films. At least 7 devices were measured on each sample in order to quantify the error in the measurements.
FIG. 2. Current density (A/mm) vs electric field (kV/cm) for a representative La:BSO film with doping densities of 2.65x10^{14} cm^{-2} (n_{3D} = 1.33x10^{19} cm^{-2}) measured using pulsed I-V for the test structure dimensions indicated.

In order to explain the mechanism of velocity saturation in these films, it is important to note that strong LO-phonon induced carrier scattering occurs in such polar materials.\textsuperscript{5, 13} We performed first-principles calculations for the phonon spectrum and electron-phonon scattering rates in BSO based on density functional theory (DFT)\textsuperscript{14,15} and density functional perturbation theory (DFPT)\textsuperscript{16} as implemented in the Quantum ESPRESSO code,\textsuperscript{17} with the generalized gradient approximation of Perdew-Burke-Ernzerhof for the exchange-correlation term.\textsuperscript{18} Optimized norm-conserving Vanderbilt pseudopotentials were employed.\textsuperscript{19} The EPW code was used to interpolate the electron-phonon matrix elements and calculate the electron-phonon scattering rates.\textsuperscript{20} The phonon spectra of BSO (Fig.S3 in the supplementary material)\textsuperscript{12} exhibits 15 branches with the three LO phonon branches (branches 6, 12 and 15) strongly affecting electron-phonon scattering for long-range Fröhlich interactions. This can be clearly seen in Fig. 3 which plots the scattering rate for the various phonon branches as a function of electron energy with reference to the Fermi level. It is evident that the scattering rate rises steeply beyond...
electron energies of 120 meV which may be taken as the net effective LO phonon energy for electron scattering due to optical phonon emission in BSO.

**FIG. 3.** Calculated electron-phonon scattering rates (in s$^{-1}$) in BSO as a function of electron energy with respect to the Fermi level (in eV). The LO phonons representing branches 6, 12 and 15 of the phonon dispersion spectra (see supplementary material)$^{12}$ play a dominant role in electron scattering with the total scattering rate increasing steeply beyond 120 meV.

Given the dominant optical phonon modes in BSO and strong LO-phonon induced carrier scattering shown above, the emission of LO-phonons by energetic carriers at the source is likely to act as the velocity saturation mechanism for BSO films. Such a model has been previously used to explain velocity saturation observed in GaN HEMTs, carbon nanotubes (CNTs) and layered materials.$^{21-24}$ To explain the model briefly, at high enough applied electric fields it becomes energetically favorable for carriers injected into the channel from the source to emit LO phonons and back-scatter back into the source region. This causes a net balance of carriers for forward injection leading to current and hence velocity saturation. The key feature of this model is the existence of a density-dependent saturation velocity as illustrated in Fig. 4 for the case of a 2-D electron gas with carrier density lower than the cross-over density ($n_0$) beyond which back-scattering into the bottom of the conduction band is not Pauli blocked. At 0 K, the Fermi circle of
radius $k_F$ indicates the range of occupied states for a given electron density. For smaller densities, we see from Fig. 4 that the carriers can be accelerated to larger velocities (higher values of charge centroid, $k_0$) before the onset of optical phonon emission takes place ($k_{op}=k_F+k_0$) as compared to lower values for higher sheet carrier densities.

**FIG. 4.** Schematic showing a comparison of electron saturation velocity due to LO phonon emission for (a) smaller and (b) larger carrier densities in terms of energy band diagrams (top) and the corresponding k-space occupation of filled electrons (bottom) denoted by Fermi circles ($k_F$) at 0K for the 2D case. $k_0$ refers to the charge centroid under high applied fields when LO-phonon emission becomes favorable ($E(k) \geq \hbar \omega_{op}$).

The total current in the device can be estimated by summing over all occupied energy levels in k-space and is given by $J=qn_s(\hbar k_0/m^*)$ for electrons in a 2DEG, where $m^*$ is the effective mass (0.2$m_0$ for BSO)\(^{25}\) and the charge centroid $k_0$ is given by $m^* \omega_{op}/2\hbar k_F$ for $n_s>n_0$ and $k_0=k_{op}+k_F$ for $n_s\geq n_0$.\(^{24}\) This gives rise to a square-root dependence between the current density and sheet carrier concentration for high densities ($n_0>n_s$) and since $J=qn_s v_{sat}$, $v_{sat}$
decreases as \( n^{-1/2} \) with increasing channel charge density. The present study, however, involved samples of fairly-thick doped-BSO films (20-25 nm) which more closely resembles a 3D electron gas rather than a 2D case. The current density for 3-D carriers can be estimated by summing the occupied states across a Fermi sphere of radius \( k_F \) as,

\[
J = q_n t \frac{\hbar}{m_e} (3\pi^2 (n_0 - n))^{1/3}, n \leq n_0
\]

\[
= \frac{q_n E_{op}}{2\hbar (3\pi^2 n)^{1/3}}, n > n_0
\]

where \( n_0 \) (= \( k_{op}^3 / 3\pi^2 \)) is the cross-over 3D density for which optical phonon emission to the bottom of the conduction band is not Pauli blocked and \( E_{op} \) is the optical phonon energy (120 meV as discussed above). The saturation velocity extracted (\( v_{sat} = J/qn_s \)) from these equations for the 3D case therefore has a \( n^{1/3} \) dependence at higher carrier densities in contrast to the \( n^{1/2} \) dependence for 2D confinement which also leads to higher values of \( v_{sat} \) in comparison.

**FIG. 5.** LO phonon-limited saturation velocity of electrons for doped-BSO 3DEG (t_{BSO} = 20 nm) and experimentally measured values with error bars for the 20 nm BSO films shown for comparison. Also shown are the density-dependent \( v_{sat} \) curves for BSO 2DEGs in the electrical quantum limit (single sub-band) and multiple sub-band contributions (t_{BSO} = 5 nm with 2 eV barriers on either side).
Fig. 5 shows the predicted saturation velocity for a range of equivalent sheet carrier concentration of the La:BSO 3DEGs along with experimentally measured values for comparison. We see that the experimentally measured saturation velocity for a range of carrier concentrations shows reasonable agreement with the predictions of the 3-D optical phonon model (at 0 K), indicating that LO-phonon emission is the likely mechanism for velocity saturation in BSO thin films. It can also be seen from Fig. 5 that the experimentally measured saturation velocity decreases for higher carrier densities as predicted by the model. Also shown is the density-dependence of saturation velocity for the 2-D case corresponding to δ-doped BSO films which are relevant for device applications as they can be pinched off using a gate bias. Since the carrier concentrations in BSO are typically much higher (>5x10^{13} cm^{-2}) than those observed in other high charge density interfaces such as AlGaN/GaN, it is important to consider not just the occupancy of the first sub-band (the electrical quantum limit), but also of higher order sub-bands which contribute to current densities and hence saturation velocity. In order to account for filling multiple sub-bands at realistic doping densities, a δ-doped BSO channel of thickness 5 nm was considered with confining barriers of 2 eV on either side, analogous to a finite potential well where each bound state represents a sub-band. The total current density was then obtained by summing up the contributions from each sub-band and the net saturation velocity is also shown in Fig. 5.\(^{12}\)

The saturation velocity for delta-doped BSO channels is estimated to drop from 1.6x10^7 cm/s to a more or less constant value of 2x10^6 cm/s for sheet carrier concentrations beyond 2x10^{14} cm^{-2}. It is evident that even though the saturation velocity drops with increasing carrier densities, the decrease is not as steep (proportional to \(n_s^{1/2}\)) as the corresponding rise in charge density (\(\sim n_s\) and hence the current drive) of BSO thin film transistors. Hence there is a definite motivation to have
highly-doped BSO channels for high charge density switches with the modulation of such large charge densities being the primary challenge for device applications.

In conclusion, we have experimentally measured the saturation velocity of La:doped-BSO thin films for a range of achievable doping densities. The experimental values show good agreement with the predictions of a LO-phonon emission model with an effective phonon energy of 120 meV, indicating the likelihood of optical phonon emission being the mechanism limiting velocity saturation in BSO thin films. Delta-doped BSO channels exhibit a density-dependent saturation velocity decreasing proportional to $n_s^{-1/2}$ from $1.6 \times 10^7$ cm/s to $2 \times 10^6$ cm$^2$/s at sheet carrier densities ranging from $10^{13}$-$2 \times 10^{14}$ cm$^{-2}$ accounting for the contribution of multiple sub-bands necessary for such high carrier densities. The estimated and measured saturation velocities presented in this work would aid in informed device design for electronics based on thin film BSO channels.

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REFERENCES:

12. see supplementary material at -- for further details.
Supplementary Material:

Velocity Saturation in La: doped BaSnO$_3$ Thin Films

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Experimental Details:

FIG. S1. SEM images of representative I-shaped constriction structures fabricated on La-doped BaSnO$_3$ films of sheet charge densities – (a) 2.65x10$^{14}$ cm$^{-2}$ ($n_{3D} = 1.33x10^{20}$ cm$^{-3}$), (b) 1.92x10$^{14}$ cm$^{-2}$ ($n_{3D} = 9.6x10^{19}$ cm$^{-3}$) and (c) 7.3x10$^{14}$ cm$^{-2}$ ($n_{3D} = 3.65x10^{19}$ cm$^{-3}$).
FIG. S2. Pulsed I-V measurements of I-shaped constriction structures of the indicated dimensions on 20 nm La-doped BaSnO$_3$ films of sheet charge density – (a) 2.65x10$^{14}$ cm$^{-2}$ ($n_{3D} = 1.33 \times 10^{20}$ cm$^{-3}$), (b) 1.92x10$^{14}$ cm$^{-2}$ ($n_{3D} = 9.6 \times 10^{19}$ cm$^{-3}$) and (c) 7.3x10$^{14}$ cm$^{-2}$ ($n_{3D} = 3.65 \times 10^{19}$ cm$^{-3}$).

Calculated Phonon Spectra of BSO:
FIG. S3. Calculated phonon spectrum of BaSnO$_3$ based on density functional perturbation theory (DFPT)$^2$ as implemented in the Quantum ESPRESSO code$^3$.

Details of the optical phonon model:

2D-case:

Current density can be obtained by summing across occupied states within a Fermi circle of radius $k_f (=\sqrt{(2\pi n_s)}$ at 0K) which for the case of a parabolic band reduces to,

$$J = \frac{2q}{(2\pi)^2} \int d^2k \left( \frac{\hbar k_0}{m^*} \right) f(k)$$

(1)

where $k_0$ is the centroid of the Fermi circle which shifts under applied bias and other terms have their usual meanings.

For carrier densities beyond cross-over 2DEG density beyond $n_0 (= k_{op}^2/8\pi)$ optical phonon emission becomes favorable and current densities have been shown to be:

$$J = q n_s \frac{\hbar (k_{op} - \sqrt{2\pi n_s})}{m^*}, n_s \leq n_0$$

(2)

$$= q \omega_{op} \frac{n_s}{\delta n}, n_s > n_0$$

2D-case with sub-bands:

The occupancy of each sub-band was estimated as $n_{k,subband i} = m^*/(\pi \hbar^2) (E_F - E_i)$ where $E_i$ refers to the bound state energy of the $i^{th}$ sub-band and the current density due to each sub-band was then estimated as above and summed to obtain the total current density.
δ-doped BaSnO$_3$ layer of thickness 5 nm and having 2 eV barriers was treated analogous to a finite potential well problem as shown in the band-diagram below.

![Band Diagram](image)

**FIG. S4.** Representative band diagram for an La:doped BSO channel (n=10$^{20}$ cm$^{-3}$) of 5 nm thickness sandwiches between two dielectric layers ($\varepsilon$=10,thickness=20 nm) having a conduction band offset of 2 eV with reference to the channel material.

The bound state solutions were obtained along the lines indicated by Chiani$^1$ (with energies of $E_1$=0.067 eV, $E_2$=0.133 eV, $E_3$=0.199 eV, $E_4$=0.265 eV, $E_5$=0.328 eV, $E_6$=0.412 eV) and were used in the current density expressions.

**3D case:**

Similar to the 2D case, the Fermi surface is a sphere at 0K for the case of a 3DEG in the thick La:doped BSO films measured here. The cross-over density for which optical phonon emission becomes favorable is then given by $n_0$ (=k$_{op}^3/3\pi^2$) and the current density itself can be estimated as,

$$J = \frac{2q}{(2\pi)^3} \int d^3k \left( \frac{\hbar^2}{m^*} \right) f(k)$$

(3)

, which then reduces to the equations given in the main text:

$$J = qnt \frac{\hbar}{m} (3\pi^2 (n_0 - n))^{\frac{1}{3}}, \ n < n_0$$

$$J = \frac{qntE_{op}}{2\hbar(3\pi^2 n)^{1/3}}, \ n > n_0$$

(4)
References:

1 Chiani, M. (2016). "A chart for the energy levels of the square quantum well". arXiv:1610.04468
